HM6216255H Series

4M high Speed SRAM (256-kword × 16-bit)

HITACHI

ADE-203-763D (Z)
Rev. 1.0
Sept. 15, 1998

Description

The HM6216255H Series is a 4-Mbit high speed static RAM organized 256-k word × 16-bit. It has realized high speed access time by employing CMOS process (4-transistor + 2-poly resistor memory cell) and high speed circuit designing technology. It is most appropriate for the application which requires high speed, high density memory and wide bit width configuration, such as cache and buffer memory in system. It is packaged in 400-mil 44-pin plastic SOJ and 400-mil 44-pin plastic TSOPII.

Features

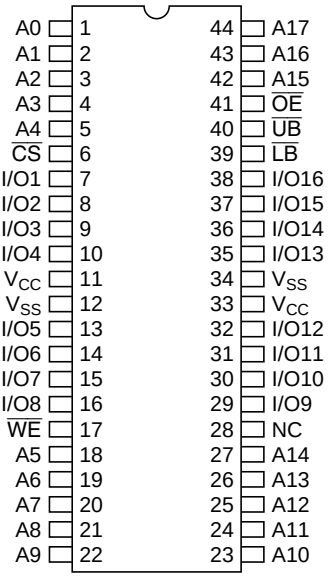
- Single 5.0 Vsupply : 5.0 V ± 10 %
- Access time: 10/12/15 ns (max)
- Completely static memory
  - No clock or timing strobe required
- Equal access and cycle times
- Directly TTL compatible
  - All inputs and outputs
- Operating current: 200/180/160 mA (max)
- TTL standby current: 70/60/50 mA (max)
- CMOS standby current: 5 mA (max)
  : 1.2 mA (max) (L-version)
- Data retention current: 0.8 mA (max) (L-version)
- Data retention voltage: 2 V (min) (L-version)
- Center V_{CC} and V_{SS} type pinout

Ordering Information

Type No.	Access time	Package
HM6216255HJP-10	10 ns	400-mil 44-pin plastic SOJ (CP-44D)
HM6216255HJP-12	12 ns	
HM6216255HJP-15	15 ns	
HM6216255HLJP-10	10 ns	
HM6216255HLJP-12	12 ns	
HM6216255HLJP-15	15 ns	
HM6216255HTT-10	10 ns	400-mil 44-pin plastic TSOPII (TTP-44DE)
HM6216255HTT-12	12 ns	
HM6216255HTT-15	15 ns	
HM6216255HLTT-10	10 ns	
HM6216255HLTT-12	12 ns	
HM6216255HLTT-15	15 ns	

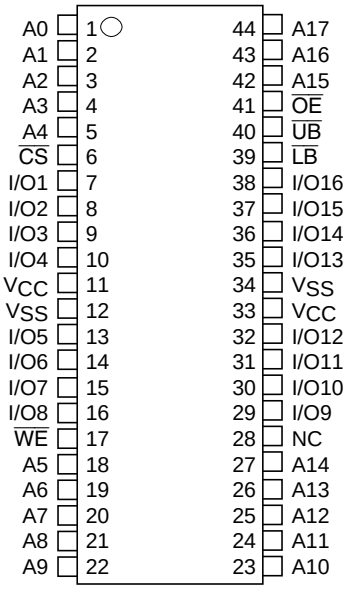
Pin Arrangement

HM6216255HJP/HLJP Series



(Top View)

HM6216255HTT/HLTT Series

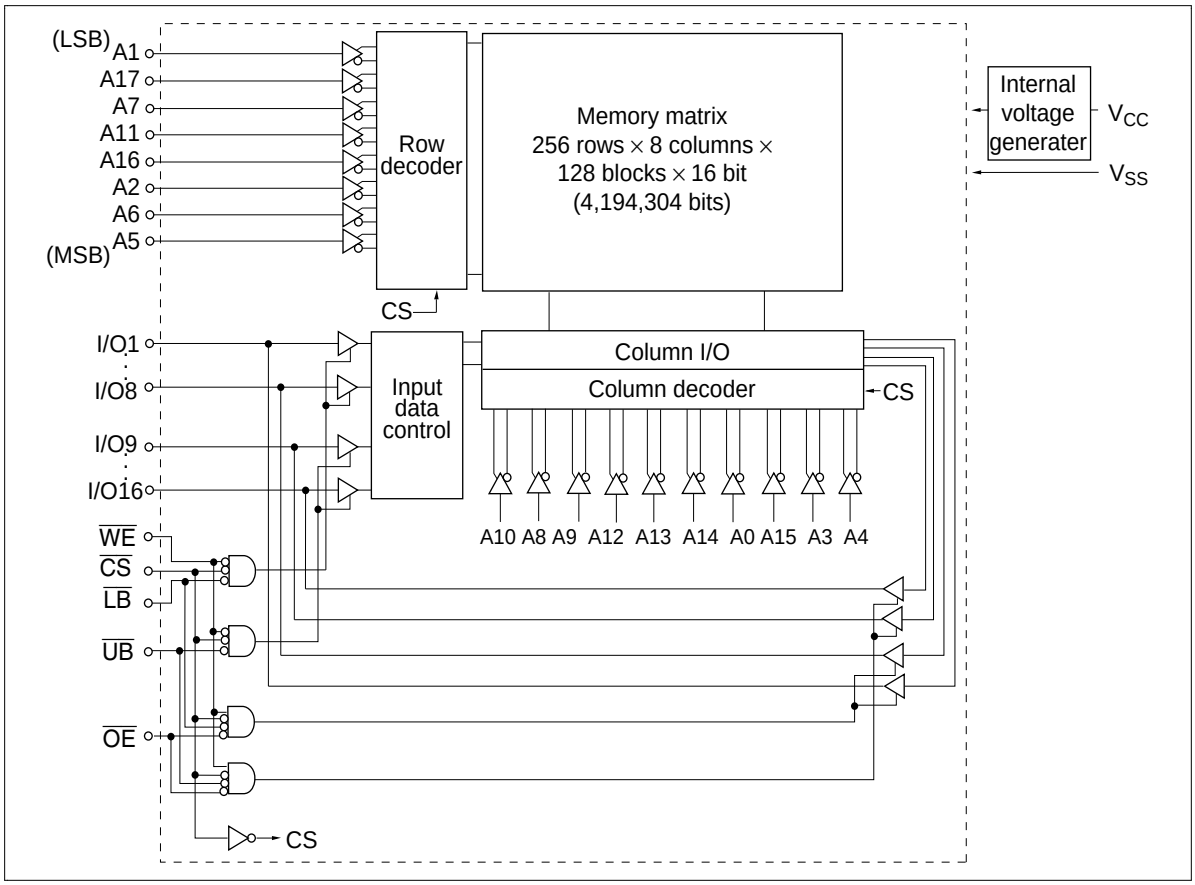


(Top View)

Pin Description

Pin name	Function	Pin name	Function
A0 to A17	Address input	$\overline{UB}$	Upper byte select
I/O1 to I/O16	Data input/output	$\overline{LB}$	Lower byte select
$\overline{CS}$	Chip select	V_{CC}	Power supply
$\overline{OE}$	Output enable	V_{SS}	Ground
$\overline{WE}$	Write enable	NC	No connection

Block Diagram



Operation Table

$\overline{CS}$	$\overline{OE}$	$\overline{WE}$	$\overline{LB}$	$\overline{UB}$	Mode	V_{CC} current	I/O1–I/O8	I/O9–I/O16	Ref. cycle
H	×	×	×	×	Standby	I_{SB}, I_{SB1}	High-Z	High-Z	—
L	H	H	×	×	Output disable	I_{CC}	High-Z	High-Z	—
L	L	H	L	L	Read	I_{CC}	Output	Output	Read cycle
L	L	H	L	H	Lower byte read	I_{CC}	Output	High-Z	Read cycle
L	L	H	H	L	Upper byte read	I_{CC}	High-Z	Output	Read cycle
L	L	H	H	H	—	I_{CC}	High-Z	High-Z	—
L	×	L	L	L	Write	I_{CC}	Input	Input	Write cycle
L	×	L	L	H	Lower byte write	I_{CC}	Input	High-Z	Write cycle
L	×	L	H	L	Upper byte write	I_{CC}	High-Z	Input	Write cycle
L	×	L	H	H	—	I_{CC}	High-Z	High-Z	—

Note: ×: H or L

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Supply voltage relative to V_{SS}	V_{CC}	–0.5 to +7.0	V
Voltage on any pin relative to V_{SS}	V_T	–0.5*[1] to V_{CC} + 0.5*[2]	V
Power dissipation	P_T	1.0*[3]/1.3*[4]	W
Operating temperature	Topr	0 to +70	°C
Storage temperature	Tstg	–55 to +125	°C
Storage temperature under bias	Tbias	–10 to +85	°C

Notes: 1. V_T (min) = –2.0 V for pulse width (under shoot) ≤ 8 ns
2. V_T (max) = V_{CC} + 2.0 V for pulse width (over shoot) ≤ 8 ns
3. At still air condition
4. At air flow ≥ 1.0 m/s

Recommended DC Operating Conditions (Ta = 0 to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{CC}*2	4.5	5.0	5.5	V
	V_{SS}*3	0	0	0	V
Input voltage	V_{IH}	2.2	—	V_{CC} + 0.5*2	V
	V_{IL}	–0.5*1	—	0.8	V

Notes: 1. V_{IL} (min) = –2.0 V for pulse width (under shoot) ≤ 8 ns
2. V_{IH} (max) = V_{CC} + 2.0 V for pulse width (over shoot) ≤ 8 ns
3. The supply voltage with all V_{CC} pins must be on the same level.
4. The supply voltage with all V_{SS} pins must be on the same level.

DC Characteristics (Ta = 0 to +70°C, V_{CC} = 5.0 V ± 10 %, V_{SS} = 0 V)

Parameter		Symbol	Min	Typ*1	Max	Unit	Test conditions
Input leakage current		$\|I_{LI}\|$	—	—	2	µA	Vin = V_{SS} to V_{CC}
Output leakage current*1		$\|I_{LO}\|$	—	—	2	µA	Vin = V_{SS} to V_{CC}
Operating power supply current	10 ns cycle	I_{CC}	—	—	200	mA	$\overline{CS}$ = V_{IL}, Iout = 0 mA Other inputs = V_{IH}/V_{IL}
	12 ns cycle	I_{CC}	—	—	180		
	15 ns cycle	I_{CC}	—	—	160		
Standby power supply current	10 ns cycle	I_{SB}	—	—	70	mA	$\overline{CS}$ = V_{IH}, Other inputs = V_{IH}/V_{IL}
	12 ns cycle	I_{SB}	—	—	60		
	15 ns cycle	I_{SB}	—	—	50		
		I_{SB1}	—	0.1	5	mA	V_{CC} ≥ $\overline{CS}$ ≥ V_{CC} – 0.2 V, (1) 0 V ≤ Vin ≤ 0.2 V or (2) V_{CC} ≥ Vin ≥ V_{CC} – 0.2 V
			—*2	0.1*2	1.2 *2		
Output voltage		V_{OL}	—	—	0.4	V	I_{OL} = 8 mA
		V_{OH}	2.4	—	—	V	I_{OH} = –4 mA

Note: 1. Typical values are at V_{CC} = 5.0 V, Ta = +25°C and not guaranteed.
2. This characteristics is guaranteed only for L-version.

Capacitance (Ta = +25°C, f = 1.0 MHz)

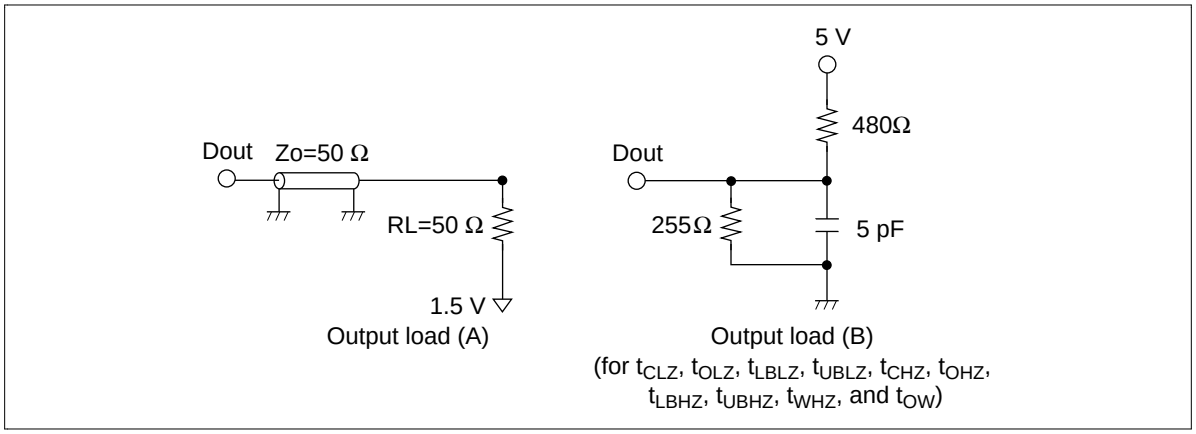
Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Input capacitance*[1]	Cin	—	—	6	pF	Vin = 0 V
Input/output capacitance*[1]	$C_{I/O}$	—	—	8	pF	$V_{I/O}$ = 0 V

Note: 1. This parameter is sampled and not 100% tested.

AC Characteristics (Ta = 0 to +70°C, V_{CC} = 5.0 V ± 10 %, unless otherwise noted.)

Test Conditions

- Input pulse levels: 3.0 V/0.0 V
- Input rise and fall time: 3 ns
- Input and output timing reference levels: 1.5 V
- Output load: See figures (Including scope and jig)



Read Cycle

		HM6216255H							
		-10		-12		-15			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
Read cycle time	t_{RC}	10	—	12	—	15	—	ns	
Address access time	t_{AA}	—	10	—	12	—	15	ns	
Chip select access time	t_{ACS}	—	10	—	12	—	15	ns	
Output enable to output valid	t_{OE}	—	5	—	6	—	7	ns	
Byte select to output valid	t_{LB}, t_{UB}	—	5	—	6	—	7	ns	
Output hold from address change	t_{OH}	3	—	3	—	3	—	ns	
Chip select to output in low-Z	t_{CLZ}	3	—	3	—	3	—	ns	1
Output enable to output in low-Z	t_{OLZ}	0	—	0	—	0	—	ns	1
Byte select to output in low-Z	t_{LBLZ}, t_{UBLZ}	0	—	0	—	0	—	ns	1
Chip deselect to output in high-Z	t_{CHZ}	—	5	—	6	—	7	ns	1
Output disable to output in high-Z	t_{OHZ}	—	5	—	6	—	7	ns	1
Byte deselect to output in high-Z	t_{LBHZ}, t_{UBHZ}	—	5	—	6	—	7	ns	1

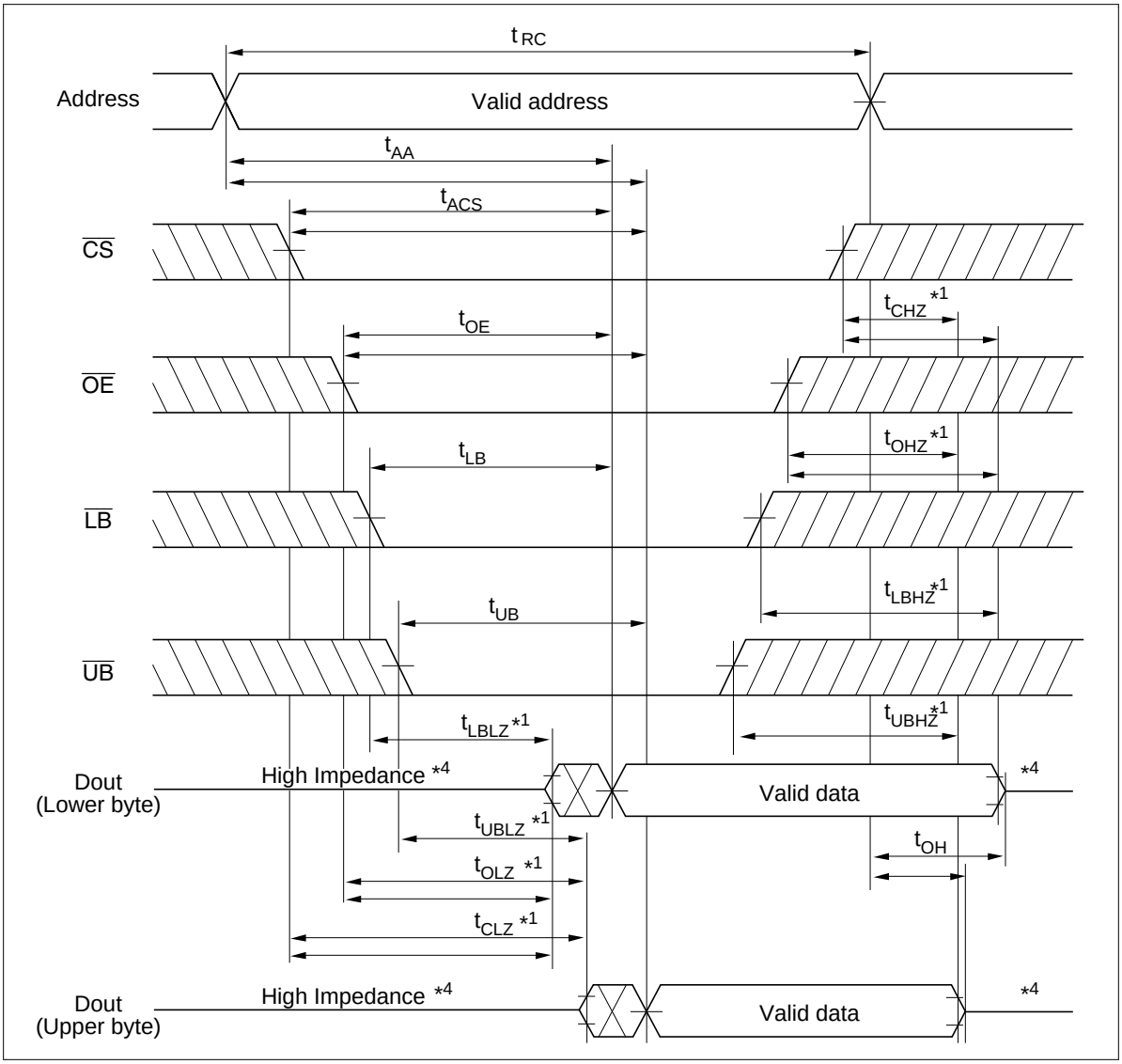
Write Cycle

		HM6216255H							
		-10		-12		-15			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
Write cycle time	t_{WC}	10	—	12	—	15	—	ns	
Address valid to end of write	t_{AW}	7	—	8	—	10	—	ns	
Chip select to end of write	t_{CW}	7	—	8	—	10	—	ns	8
Write pulse width	t_{WP}	7	—	8	—	10	—	ns	7
Byte select to end of write	t_{LBW}, t_{UBW}	7	—	8	—	10	—	ns	9, 10
Address setup time	t_{AS}	0	—	0	—	0	—	ns	5
Write recovery time	t_{WR}	0	—	0	—	0	—	ns	6
Data to write time overlap	t_{DW}	5	—	6	—	7	—	ns	
Data hold from write time	t_{DH}	0	—	0	—	0	—	ns	
Write disable to output in low-Z	t_{OW}	3	—	3	—	3	—	ns	1
Output disable to output in high-Z	t_{OHZ}	—	5	—	6	—	7	ns	1
Write enable to output in high-Z	t_{WHZ}	—	5	—	6	—	7	ns	1

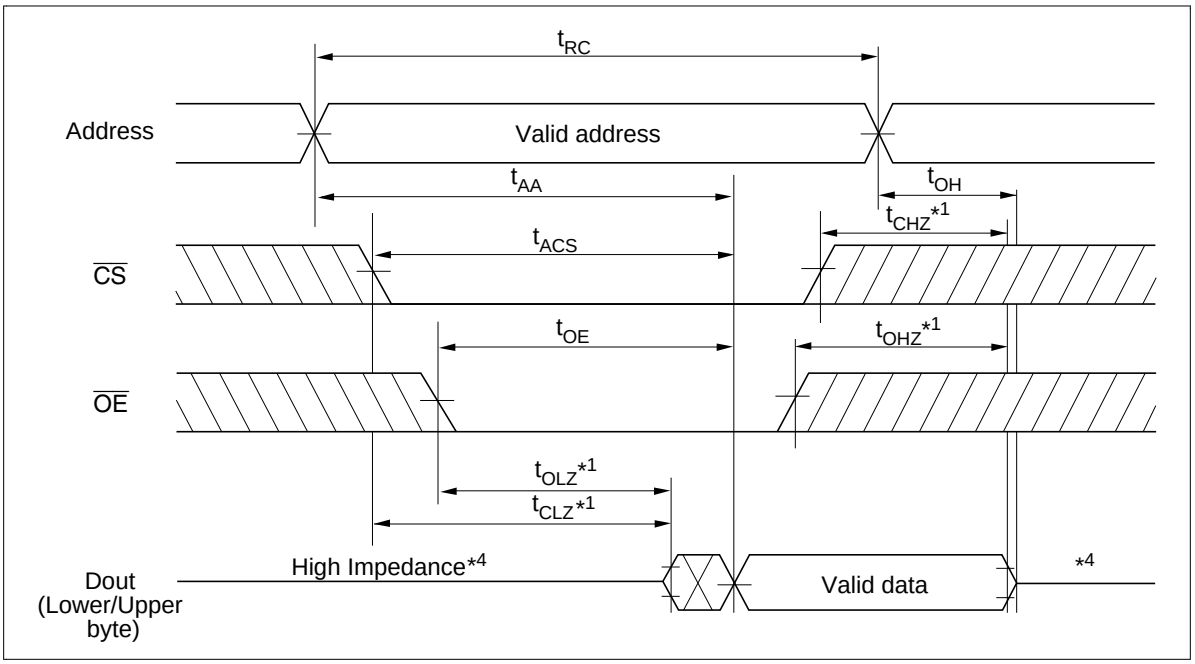
Notes:
1. Transition is measured ±200 mV from steady voltage with Load (B). This parameter is sampled and not 100% tested.
2. If the $\overline{CS}$ or $\overline{LB}$ or $\overline{UB}$ low transition occurs simultaneously with the $\overline{WE}$ low transition or after the $\overline{WE}$ transition, output remains a high impedance state.
3. $\overline{WE}$ and/or $\overline{CS}$ must be high during address transition time.
4. If $\overline{CS}$, $\overline{OE}$, $\overline{LB}$ and $\overline{UB}$ are low during this period, I/O pins are in the output state. Then the data input signals of opposite phase to the outputs must not be applied to them.
5. t_{AS} is measured from the latest address transition to the latest of $\overline{CS}$, $\overline{WE}$, $\overline{LB}$ or $\overline{UB}$ going low.
6. t_{WR} is measured from the earliest of $\overline{CS}$, $\overline{WE}$, $\overline{LB}$ or $\overline{UB}$ going high to the first address transition.
7. A write occurs during the overlap of low $\overline{CS}$, low $\overline{WE}$ and low $\overline{LB}$ or low $\overline{UB}$.
8. t_{CW} is measured from the later of $\overline{CS}$ going low to the end of write.
9. t_{LBW} is measured from the later of $\overline{LB}$ going low to the end of write.
10. t_{UBW} is measured from the later of $\overline{UB}$ going low to the end of write.

Timing Waveforms

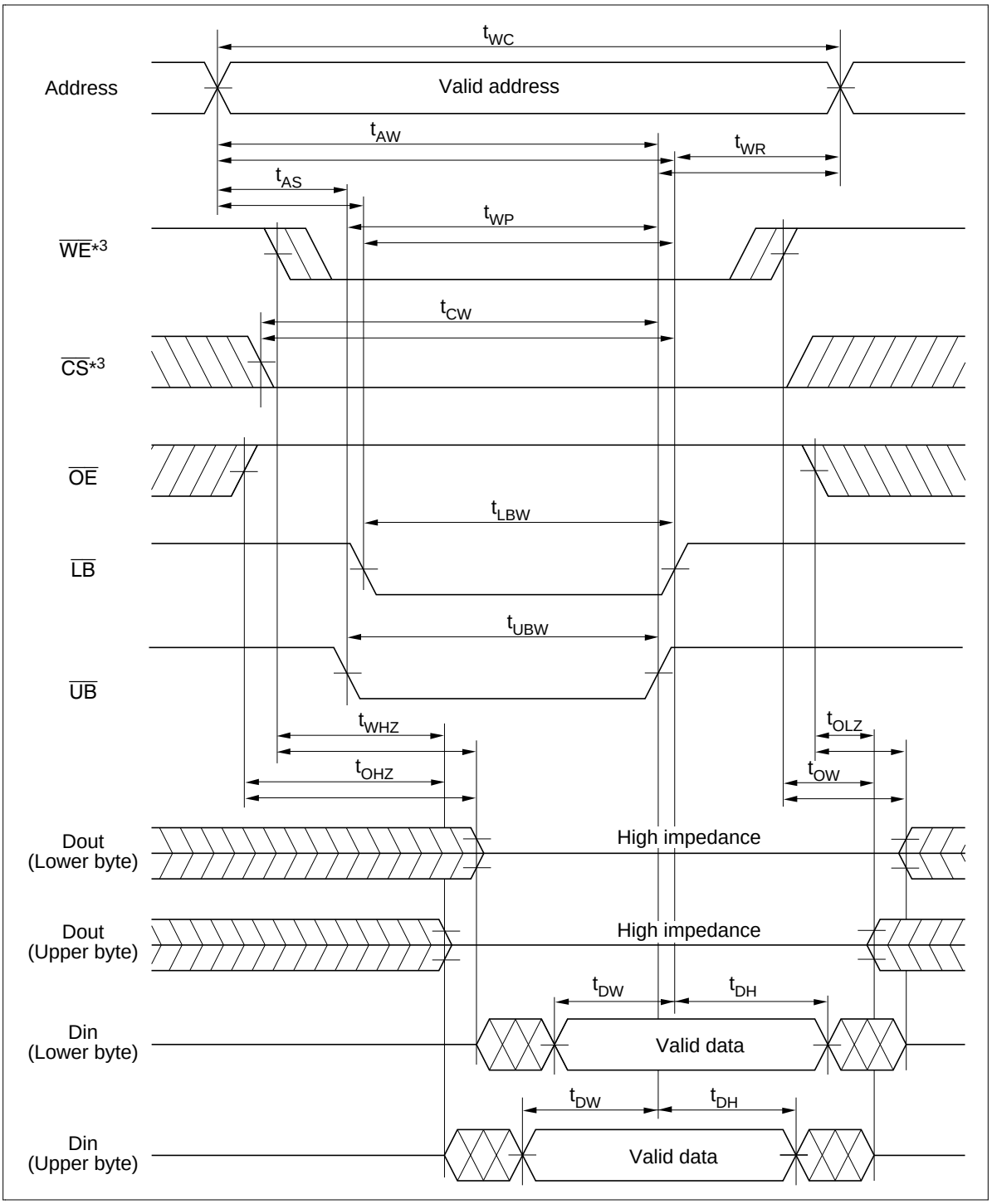
Read Timing Waveform (1) ($\overline{WE}$ = V_{IH})



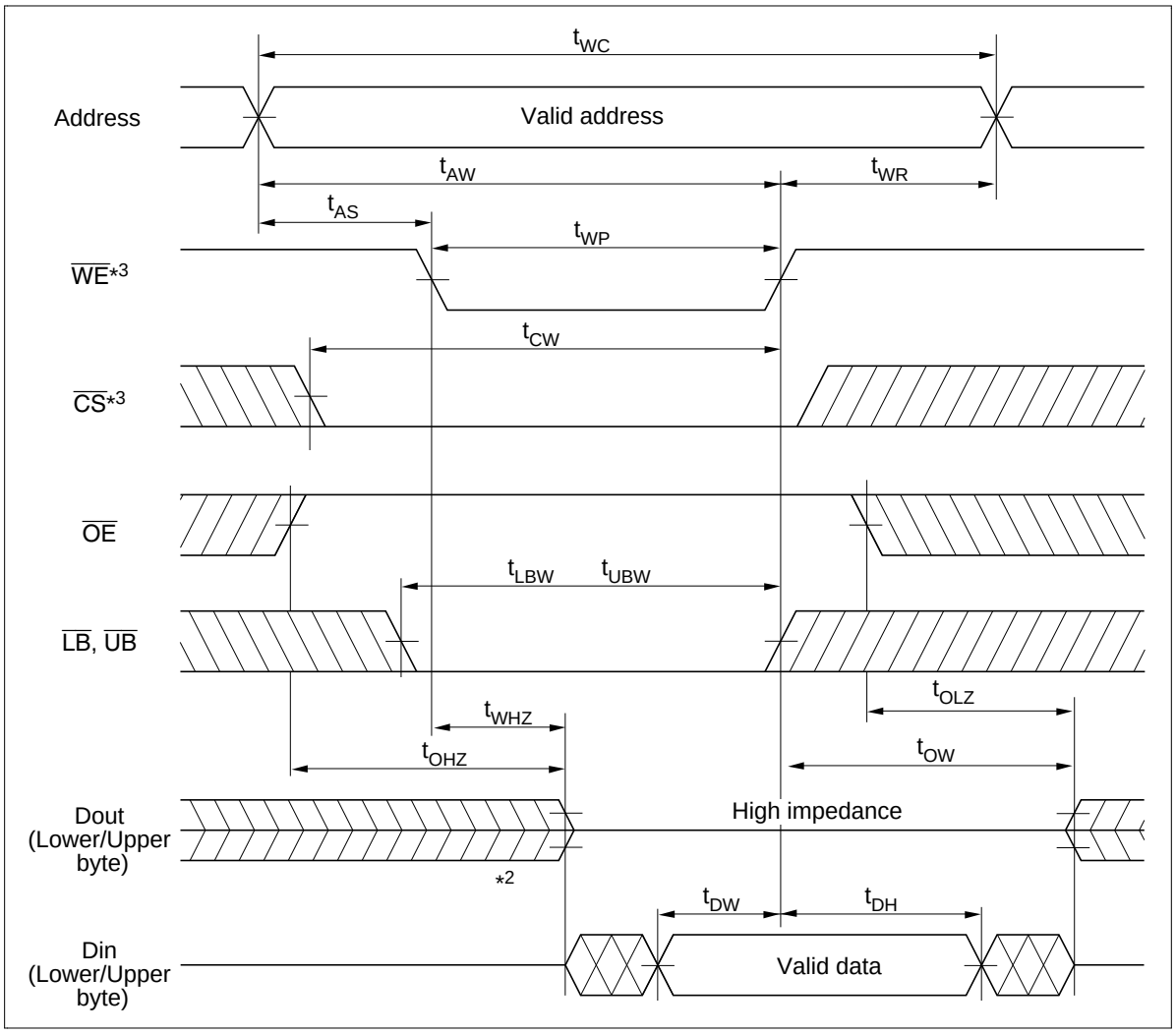
Read Timing Waveform (2) ($\overline{WE}$ = V_{IH}, $\overline{LB}$ = V_{IL}, $\overline{UB}$, = V_{IL})



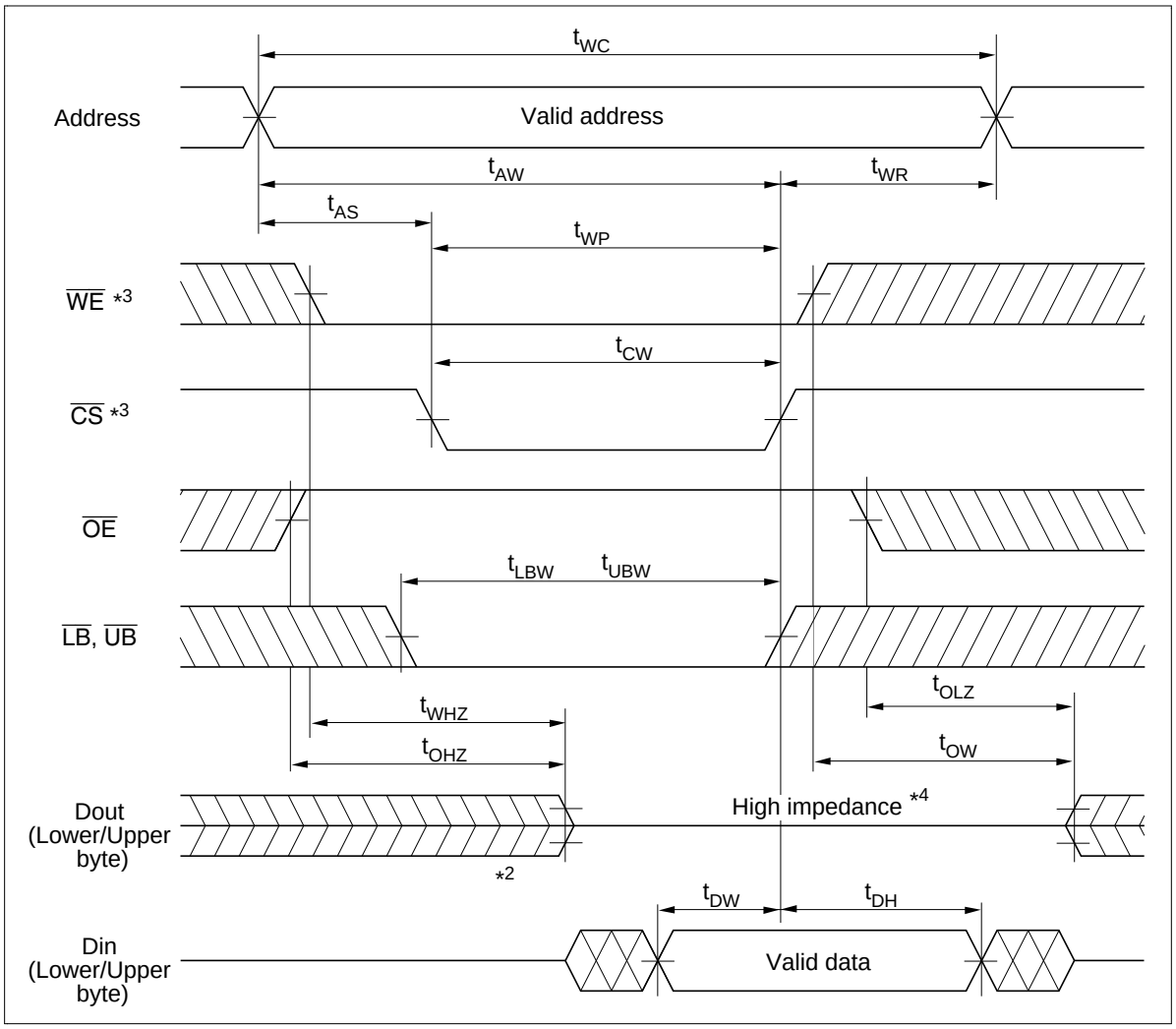
Write Timing Waveform (1) ($\overline{LB}$, $\overline{UB}$ Controlled)



Write Timing Waveform (2) ($\overline{WE}$ Controlled)



Write Timing Waveform (3) ($\overline{CS}$ Controlled)



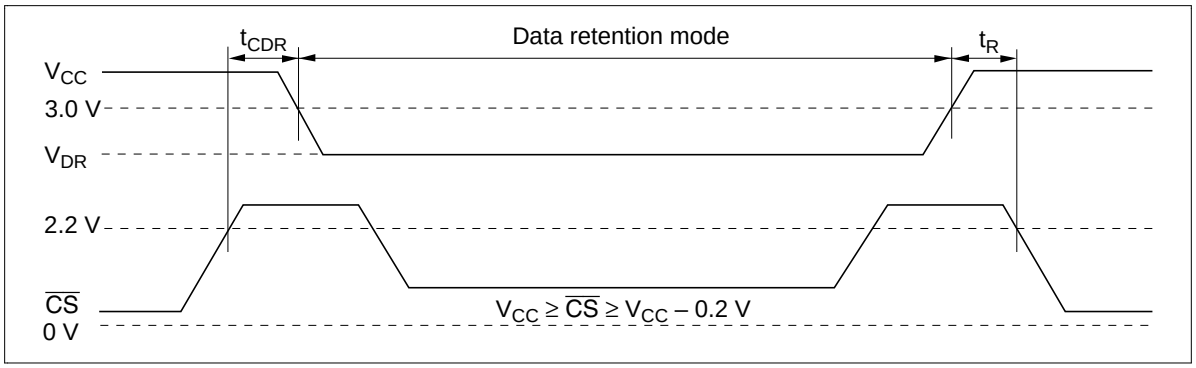
Low V_{CC} Data Retention Characteristics (Ta = 0 to +70°C)

This characteristics is guaranteed only for L-version.

Parameter	Symbol	Min	Typ*[1]	Max	Unit	Test conditions
V_{CC} for data retention	V_{DR}	2.0	—	—	V	$V_{CC} \geq \overline{CS} \geq V_{CC} - 0.2$ V, (1) 0 V ≤ Vin ≤ 0.2 V or (2) $V_{CC} \geq$ Vin ≥ $V_{CC} - 0.2$ V
Data retention current	I_{CCDR}	—	50	800	µA	V_{CC} = 3 V $V_{CC} \geq \overline{CS} \geq V_{CC} - 0.2$ V, (1) 0 V ≤ Vin ≤ 0.2 V or (2) $V_{CC} \geq$ Vin ≥ $V_{CC} - 0.2$ V
Chip deselect to data retention time	t_{CDR}	0	—	—	ns	See retention waveform
Operation recovery time	t_R	5	—	—	ms	

Note: 1. Typical values are at V_{CC} = 3.0 V, Ta = +25°C, and not guaranteed.

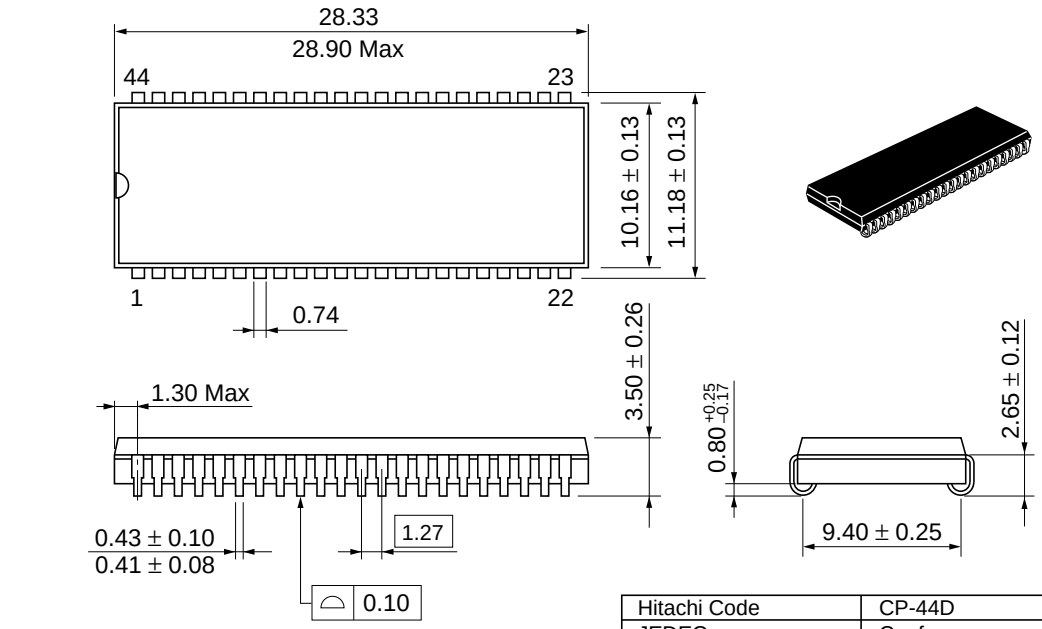
Low V_{CC} Data Retention Timing Waveform



Package Dimensions

HM6216255HJP/HLJP Series (CP-44D)

Unit: mm

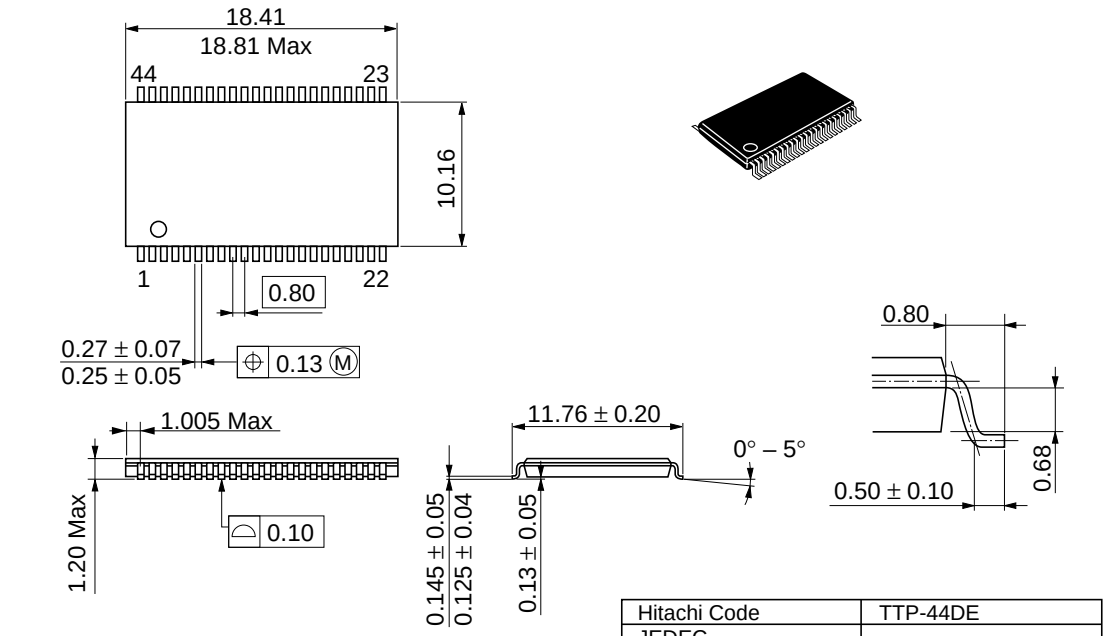


Dimension including the plating thickness
Base material dimension

Hitachi Code	CP-44D
JEDEC	Conforms
EIAJ	—
Weight (reference value)	1.8 g

HM6216255HTT/HLTT Series (TTP-44DE)

Unit: mm



Dimension including the plating thickness
Base material dimension

Hitachi Code	TTP-44DE
JEDEC	—
EIAJ	—
Weight (reference value)	0.43 g

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Revision Record

Rev.	Date	Contents of Modification	Drawn by	Approved by
0.0	Mar. 27, 1997	Initial issue	Y. Saitoh	A. Ide
0.1	Nov. 20, 1997	Change of subtitle	K. Makuta	K. Makuta
0.2	Dec. 5, 1997	Features Addition of Operating current Addition of TTL standby current Addition of CMOS standby current Addition of Data retention current Addition of Data retention voltage Change of Block Diagram Absolute Maximum Ratings P_T: 1.0/1.5 W to 1.0/1.3 W Change of notes Recommended DC Operating Conditions Change of notes DC Characteristics I_{CC} (max): 300/270/250 mA to 220/190/160 mA I_{SB} (max): 100/100/100 mA to 60/50/40 mA I_{SB1} (max): 10/1 mA to 5/1 mA AC Characteristics Change of Output load (A) t_{OE}, t_{LB}, t_{UB}, t_{CHZ}, t_{OHZ}, t_{LBHZ} and t_{UBHZ} (max): 5/6/8 ns to 5/6/7 ns t_{AW}, t_{CW}, t_{WP}, t_{LBW} and t_{UBW} (min): 6/8/10 ns to 7/8/10 ns t_{DW} (min): 5/6/8 ns to 5/6/7 ns t_{OHZ} and t_{WHZ} (max): 5/6/8 ns to 5/6/7 ns Low V_{CC} Data Retention Characteristics I_{CCDR}: —/2/300 µA to —/—/300 µA Change of Low V_{CC} Data Retention Timing Waveform	T. Fukazawa	K. Makuta
0.3	May. 15, 1998	Features Change of Operating current Change of TTL standby current Change of Block Diagram DC Characteristics I_{CC} (max): 220/190/160 ns to 200/180/160 ns I_{SB} (max): 60/50/40 ns to 70/60/50 ns Addition of Package Dimensions (TTP-44DE)	T. Fukazawa	K. Makuta
1.0	Sep. 15, 1998	Features Change of CMOS standby current (L-version) Change of Data retention current DC Characteristics I_{SB1} (max): 5/1 mA to 5/1.2 mA I_{SB1} (typ): —/— mA to 0.1/0.1 mA Low V_{CC} Data Retention Characteristics I_{CCDR}: —/—/300 µA to —/50/800 µA		